Vishay Siliconix

New Product

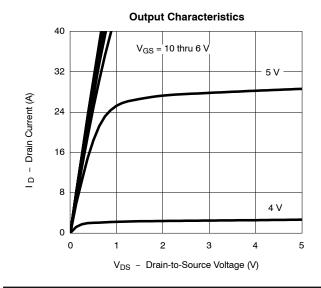


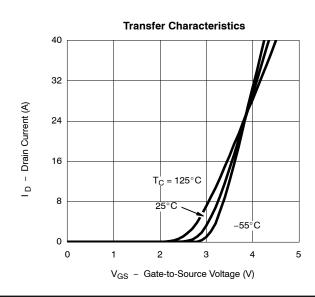
SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static						•
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1		3	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 40 V, V _{GS} = 0 V			1	μΑ
		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			5	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 10.2 A		0.016	0.019	Ω
		$V_{GS} = 4.5 \text{ V, } I_D = 8.7 \text{ A}$		0.021	0.026	
Forward Transconductancea	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 10.2 \text{ A}$		26		S
Diode Forward Voltage ^a	V _{SD}	I _S = 2.9 A, V _{GS} = 0 V		0.8	1.2	V
Dynamic ^b						
Total Gate Charge	Q_g	V_{DS} =20 V, V_{GS} = 10 V, I_{D} = 10.2 A		23	35	nC
Gate-Source Charge	Q _{gs}			4.4		
Gate-Drain Charge	Q_{gd}			5.6		
Gate Resistance	R _g	f = 1 MHz	1	2.3	3.9	Ω
Turn-On Delay Time	t _{d(on)}	V_{DD} = 20 V, R_L = 20 Ω $I_D \cong 1$ A, V_{GEN} = 10 V, R_g = 6 Ω		15	25	ns
Rise Time	t _r			15	25	
Turn-Off Delay Time	t _{d(off)}			50	75	
Fall Time	t _f			16	25	
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.9 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		30	60	1

Notes

- Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2%.
- b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

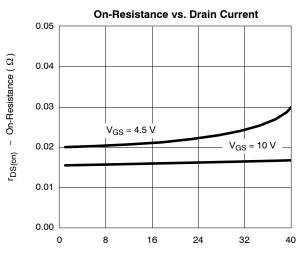








TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

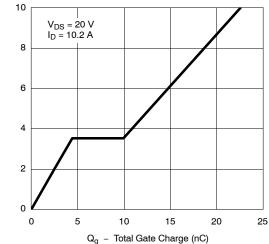




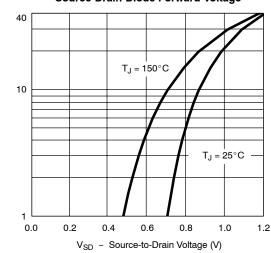


r_{DS(on)} - On-Resiistance (Normalized)

¹DS(on) - On-Resistance (᠒)

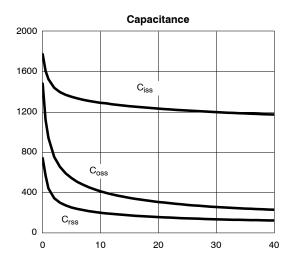


Source-Drain Diode Forward Voltage



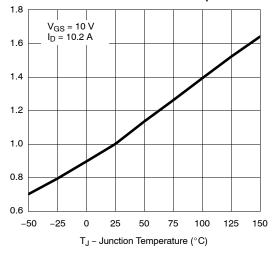
C - Capacitance (pF)

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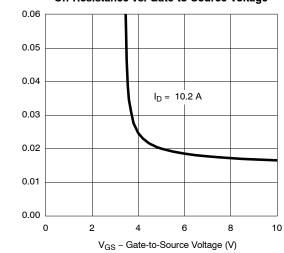


V_{DS} - Drain-to-Source Voltage (V)

On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Source Current (A)

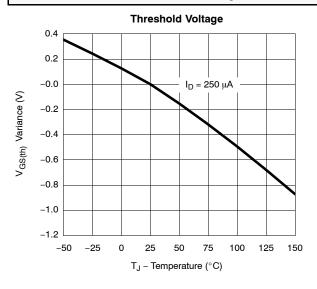
V_{GS} - Gate-to-Source Voltage (V)

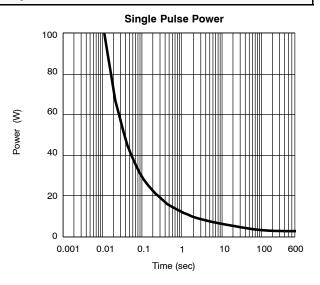
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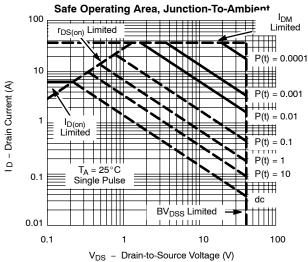
New Product



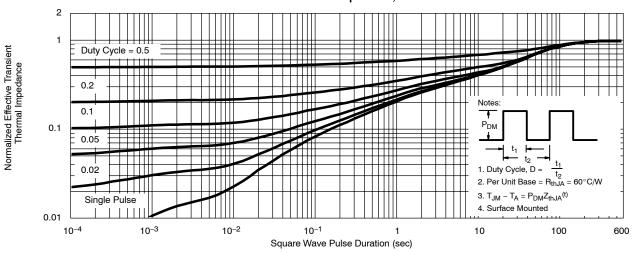
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)







Normalized Thermal Transient Impedance, Junction-to-Ambient

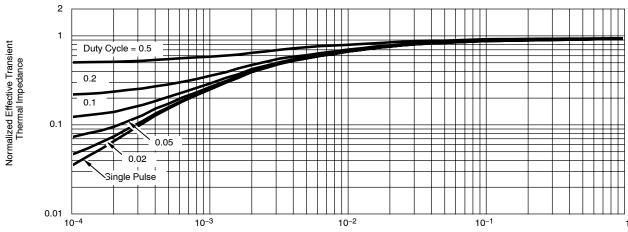


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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Normalized Thermal Transient Impedance, Junction-to-Case

New Product



Square Wave Pulse Duration (sec)



Vishay

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